



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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4-1-03  
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In re the Application of: )  
OKU et al ) Examiner: Dang, T.  
Serial No.: 09/903,764 ) Art Unit: 2823  
Filed: July 13, 2001 )  
For: FILM FORMING METHOD, SEMICONDUCTOR )  
DEVICE AND SEMICONDUCTOR DEVICE )  
MANUFACTURING METHOD )

RESPONSE TO OFFICE ACTION OF OCTOBER 24, 2002

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Responsive to the office action of October 24, 2002, please amend the captioned application as follows:

RECEIVED  
MAR 28 2003  
TECHNICAL STAFF  
MAR 28 2003

IN THE CLAIMS:

Please cancel claims 6 and 7 and rewrite claims 1-5 and 8 as follows:

1. (Amended) A film forming method for forming a silicon-containing barrier insulating film on a substrate comprising the steps of:

b' (a) preparing a film-forming gas comprising, (1) at least one member selected from the group consisting of alkoxy compounds having Si-H bonds and siloxane compounds having Si-H